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SCTATEMENT DV ADDI ICANIT	Filing Dat	December 29, 2000		
STATEMENT BY APPLICANT	First Named Inventor	Robert A. Morgan		
TATA DE	Art Unit	2814		

Fling Dat December 29, 2000

First Named Inventor Robert A. Morgan

Art Unit 2814

Examiner Name Douglas A. Willie

Attorney Docket Number H16 26549 US

	Cite No.1		Document N	umber	5 AN. D. S.	N	Pages, Columns, Lines Where
Examiner Initials*			Number	Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Relevant Passages or Relevan Figures Appear
Delle		US 5,034,958		07-23-1991	Kwon et al.		
7		US	5,258,316	Α	11-02-1993	Ackley et al.	
		US	6,026,111	Α	02-15-2000	Jiang et al.	
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	No.1	Country Code ³	Number ⁴	Kind Code ³ (If known)	MM-DD-YYYY	Document	Passages or Relevant Figures Appear	
	1	EP	0 712 182	A2	05-15-1996	Sharp Kabushiki Kaisha		
	-	FR	2 768 566	A1	03-19-1999	France Telecon Society Anonyme		
-T		wo	99/031735	A1	06-24-1999	Honeywell Inc.		
- (-	7	wo	00/045483	A1	08-03-2000	University of Sheffield		

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NFORMATION DISCLOSURE	Filing Date	December 29, 2000	
STATEMENT BY APPLICANT	First Named Inventor	Robert A. Morgan	
(USE AS MANY SHEETS AS NECESSARY)	Group Art Unit	2814	
Sheet 2 Of 2	Examiner Name	Douglas A. Willie	
	Attorney Docket Number	H16 26549 US	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²
Dhe		International Search Report, dated 03-12-2003, relative to PCT application No. PCT/US 01/50214, the foreign equivalent to the Instant U.S. application 09/751,423.	
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FORM PTO-1449	Atty. Docket No.: Serial No.: 1100.1114101 (H16-26549) 09/751,423 Applicant: Robert A. Morgan et al.		
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C. TRAD	MARKS	y
Defu	ВВ	Choquette et al., "Lithographically-Defined Gain Apertures Within Selectively Oxidized VCSELs", paper CtuL6, Conference on Lasers and Electro-Optics, San Francisco, California (2000).
\cdot	вС	Oh, T. H. et al., "Single-Mode Operation in Antiguided Vertical-Cavity Surface-Emitting Laser Using a Low-Temperature Grown AlGaAs Dielectric Aperture", <u>IEEE Photon. Technol. Lett.</u> 10(8), 1064-1066 (1998).
5	BD	"Surface-Emitting Microlasers for Photonic Switching and Interchip Connections", Optical Engineering, 29, pp. 210-214, March 1990.
	BE	G. Shtengel et al., "High-Speed Vertical-Cavity Surface-Emitting Lasers", Photon. Tech. Lett., Vol. 5, No. 12, pp. 1359-1361 (December 1993).
	De file	BC

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LISTOP RATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION	Applicant: Robert A. Morgan et al.		
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U.S. PATENT DOCUMENTS

	RADEMARK		U.S.	PATENT DOCUMEN	18		
	miner itial	Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate
1stu	AA	4,317,085	02/23/1982	Brunham et al.	372	50	
	AB	4,466,694	08/21/1984	MacDonald	385	37	
\perp	AC	4,660,207	04/21/1987	Svilans	372	45	
$\int_{-\infty}^{\infty}$	AD	4,784,722	11/15/1988	Liau et al.	156	649	
\perp	AE	4,885,592	12/05/1989	Kofol et al.	343	753	
	AF	4,901,327	02/13/1990	Bradley	372	45	
	AG	4,943,970	07/24/1990	Bradley	372	45	
	AH	4,956,844	09/11/1990	Goodhue et al.	372	44	
T	AI	5,031,187	07/09/1991	Orenstein et al.	372	50	
T	AJ	5,052,016	09/24/1991	Mahbobzadeh	372	96	
T	AK	5,056,098	10/08/1991	Anthony et al.	372	45	
	AL	5,062,115	10/29/1991	Thornton	372	50	
	AM	5,068,869	11/26/1991	Wang et al.	372	45	
	AN	5,115,442	05/19/1992	Lee et al.	372	45	
	AO	5,140,605	08/18/1992	Paoli et al.	372	50	
	AP	5,158,908	10/27/1992	Blonder et al.	437	129	
T	AQ	5,216,263	06/01/1993	Paoli	257	88	
T	AR	5,216,680	06/01/1993	Magnusson et al.	372	20	
	AS	5,237,581	08/17/1993	Asada et al.	372	45	
	AT	5,245,622	09/14/1993	Jewell et al.	372	45	
	AU	5,258,990	11/02/1993	Olbright et al.	372	46	
\	AV	5,285,466	02/08/1994	Tabatabaie	372	92	
1	AW	5,293,392	03/08/1994	Shieh et al.	372	45	
T	AX	5,317,170	05/31/1994	Paoli	257	88	
1	AY	5,317,587	05/31/1994	Ackley et al.	372	45	

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Atty. Docket No.:
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Applicant: Robert A. Morgan et al.

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Applicant: Robert A. Morgan et al.

Applicant: Robert A. Morgan et al.

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Exam Init		Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate
The	ΑZ	5,325,386	06/28/1994	Jewell et al.	372	50	
	BA	5,331,654	07/19/1994	Jewell et al.	372	45	
	BB	5,337,074	08/09/1994	Thornton	346	107R	
$\Box I$	вс	5,349,599	09/20/1994	Larkins	372	50	
	BD	5,351,256	09/27/1994	Schneider et al.	372	45	
	BE	5,359,447	10/25/1994	Hahn et al.	359	154	
	BF	5,359,618	10/25/1994	Lebby et al.	372	45	
	BG	5,363,397	11/08/1994	Collins et al.	372	92	
	вн	5,373,520	12/13/1994	Shoji et al.	372	45	
	BI	5,404,373	04/04/1995	Cheng	372	50	
	вл	5,416,044	05/16/1995	Chino et al.	437	129	
	вк	5,428,634	06/27/1995	Bryan et al.	372	45	
	BL	5,446,754	08/29/1995	Jewell et al.	372	50	
	вм	5,475,701	12/12/1995	Hibbs-Brenner	372	50	
	BN	5,513,202	04/30/1996	Kobayashi et al.	372	96	
	во	5,530,715	06/25/1996_	Shieh et al.	372	96	
	ВР	5,555,255	09/10/1996	Kock et al.	372	96	
	BQ	5,557,626	09/17/1996	Grodinski et al.	372	45	
	BR	5,561,683	10/01/1996	Kwon	372	96	
	BS	5,568,499	10/22/1996	Lear	372	45	
	вт	5,598,300	01/28/1997	Magnusson et al.	359	566	
	BU	5,606,572	02/25/1997	Swirhun et al.	372	96	
\int	BV	5,642,376	06/24/1997	Olbright et al.	372	45	
I	вw	5,727,013	03/10/198	Botez et al.	372	96	
	вх	5,774,487	06/30/1998	Morgan	372	45	

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FORM PTO-1449	Atty. Docket No.: 1100.1114101 (H16-26549)	Serial No.: 09/751,423	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION	Applicant: Robert A. Morgan et al.		
DISCLOSURE STATEMENT	Filing Date	Group Art:	
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FOREIGN PATENT DOCUMENTS

•		Document No.	Date	Country	Class	Sub Class	Translation Yes No		
Thei	AA	DE 4 240 706 A	06/09/1994	Germany					
	AB	EP 0 288 184 A	10/26/1988	Europe					
)	AC	EP 0 776 076 A	05/28/1997	Europe					
	AD	JP 60-123084 A	07/01/1985	Japan			Yes (Abstract only		
\mathcal{I}	AE	JP 02-054981 A	02/23/1990	Japan			Yes (Abstract only		
	AF	Guenter et al., "Relia SPIE, Vol. 2683, OE	ability of Proton-	uthor, Title, Date, Per Implanted VCSELs for poinces West: Fabrication (Page 1996)	or Data Com	munication	ns", Invited paper, lity of		
1	AG	Semiconductor Lasers, (SPIE, Bellingham, WA 1996). Hibbs-Brenner et al., "Performance, Uniformity and Yield of 850nm VCSELs Deposited by MOVPE", IEEE Phot. Tech. Lett., Vol. 8, No. 1, pp. 7-9, January 1996.							
AH Hor		Homak et al "Low-	Hornak et al., "Low-Termperature (10K-300K) Characterization of MOVPE-Grown Vertical-Cavity Surface-Emitting Lasers", Photon. Tech. Lett., Vol. 7, No. 10, pp. 1110-1112, October						
	AI	Huffaker et al., "Lasi Spacer Layers and L April 3, 1995.	ing Characteristi ateral Index Con	cs of Low Threshold National finement", <u>Appl. Phys</u>	Microcavity la. Lett., Vol.	Layers Usi 66, No. 14	ng Half-Wave , pp.1723-1725,		
10	AJ	K.L. Lear et al., "Selectively Oxidized Vertical Cavity Surface-Emitting Lasers with 50% Power Conversion Efficiency", Elec. Lett., Vol. 31, No. 3 pp. 208-209, February 2, 1995.							
	AK	Lehman et al., "High Singlemode VCSEL:	Frequency Mod s", Electronic Le	ulation Characteristic tters, vol. 31, No. 15,	s of Hybrid I July 20, 199	Dielectric/2 5, pp. 1251	AlGaAs Mirror I-1252.		
	AL	Magnusson, "Integra Research Center, De 1997.	tion of Guided-N partment of Elec	Mode Resonance Filter trical Engineering, Un	rs and VCSE iversity of T	Ls", Elect exas at Ar	o-Optics lington, May 6,		
	AM	Morgan et al., "Hybr Laser", Appl. Phys. I	id Dielectric/Al(<u>_ett.</u> , Vol. 60, No	GaAs Mirror Spatially b. 8, pp. 921-923, Feb	Filtered Ver uary 24, 199	tical Top-	Surface Emitting		
1 1	AN	Morgan et al., "One pp. 206-207, January	Watt Vertical Ca	vity Surface Emitting	Laser", Elec	tron. Lett.	, Vol. 29, No. 2,		

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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E.	THAI ()-f	AO	Morgan et al., "Producible GaAs-based MOVP Lasers with Record Performance", Elec. Lett., '	E-Grown Vertical-Cavity Top Vol. 31, No. 6, pp. 462-464, M	-Surface Emitting Iarch 16, 1995.	
0	1.	AP	Morgan et al., "Spatial-Filtered Vertical-Cavity 138-139.			
•)	AQ	Morgan et al., "Vertical Cavity Surface Emittin paper, SPIE, Vol. 2683-04, OE LASE 96; Photo Semiconductor Lasers, (SPIE< Bellingham, Warners)	onics West: Frabrication, Test	e,", Invited ting and Reliablity of	
•		AR	S.S. Wang and R. Magnusson, "Multilayer Wav 14, pp. 2414-20, 1995.	veguide-Grating Filters", Appl	l. Opt., Vol. 34, No.	
		AS	S.S. Wang and R. Magnusson, "Theory and Ap Appl. Opt., Vol. 32, No. 14, pp. 2606-13, 1993.		esonance Filters",	
		AT	Schubert, "Resonant Cavity Light-Emitting Dic February 24, 1992.	ode", Appl. Phys. Lett., Vol. 60	0, No. 8, pp. 921-923,	
	\perp	AU	Y. M. Yang et al., "Ultralow Threshold Current with Selective Oxidation", Elect. Lett., Vol. 31	Vertical Cavity Surface Emit , No. 11, pp. 886-888, May 25	ting Lasers Obtained 5, 1995.	
		AV	Yablonovitch et al., "Photonic Bandgap Structu 295, February 1993.	res", <u>J. Opt. Soc. Am. B.,</u> Vol	. 10, No. 2, pp. 283-	
		AW	Young et al., "Enhanced Performance of Offset Emitting Lasers", IEEE J. Quantum Electron.,	-Gain High Barrier Vertical-C Vol. 29, No. 6, pp. 2013-2022,	avity Surface- June 1993.	
		AX	Smith, R.E. et al., "Polarization-Sensitive Subw Semiconductor for 975 NM, Optics Letters, Vo	vavelength Antireflection Surfall. 21, No. 15, August 1, 1996,	aces on a pp. 1201-1203.	
-		AY	Suning Tang et al., "Design Limitations of High on Arrays of Vertical Cavity Surface-Emitting I Journal of Lightwave Technology, Vol. 12, No.	Laser Diodes, Microlenses, an	d Photodetectors",	
		AZ	Cox, J. A., et al., "Guided Mode Grating Reson of the SPIE, The International Society for Optic Technologies and Applications V, San Jose, Ca 71.	al Engineering, Diffractive an	d Holographic Device	
0		ВА	Martinsson et al., "Transverse Mode Selection i Surface-Emitting Lasers Using a Shallow Surfa 1536-1538 (1999).	n Large-Area Oxide-Confined ce Relief', <u>IEEE Photon. Tech</u>	l Vertical-Cavity mol. Lett., 11(12),	

EXAMINER: Description of the Date Considered in the Date Considered. Include copy of this form with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

	FOR	M PTO	D-1449	Atty. Docket No.: 1100.1114101 (H16-26549)	Serial No.: 09/751,423	
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	.uc 1	9 2083	Spisclosure Statement	Filing Date	Group Art:	
É			§	December 29, 2000	2872	
4	Spec.	CM	Jewell et al., "Surface-Emitting Microlasers for Optical Engineering, Vol. 29, No. 3, March 199	Photonic Switching and Inter	chip Connections",	
0	•)	CN	Kishino et al., "Resonant Cavity-Enhanced (RC Electronics, Vol. 27, No. 8, pp. 2025-2034.		mal of Quantum	
<i>c</i>	• [со	Kuchibhotla et al., "Low-Voltage High Gain Re Phototonics Technology Letters, Vol. 3, No. 4,	esonant_Cavity Avalanche Phopp. 354-356.	otodiode", <u>IEEE</u>	
c'	L	CP	Lai et al., "Design of a Tunable GaAs/AlGaAs Photodetector", IEEE Journal of Quantum Elec			
c _	1	cq	Lee et al., "Top-Surface Emitting GaAs Four-Q Electronics Letters, Vol. 24, No. 11, May 24, 19		at 0-85 um",	
<i>o</i> _		CR	Lehman et al., "High Frequency Modulation Ch Singlemode VCSELs", Electronic Letters, vol.			
l: 		cs	Miller et al., "Optical Bistability Due to Increas 1984, pp. 162-164.	ing Absorption", Optics Lette	rs, Vol. 9, No. 5, May	
о —		СТ	Morgan et al., "200 C, 96-nm Wavelength Rang MOVPE-Grown Vertical Cavity Surface-Emitti Vol. 7, No. 5, May 1995, pp. 441-443.	ge, Continuous-Wave Lasing fing Lasers", <u>IEEE Photonics T</u>	rom Unbonded GaAs echnology Letters,	
c -		CU	Jiang et al., "High-Frequency Polarization Self- Lasers", Appl. Phys. Letters, Vol. 63, No. 26, D	Modulation in Vertical-Cavity December 27, 1993, pp. 2545-2	Surface-Emitting	
0 		cv	Morgan et al., "High-Power Coherently Couple Array", Appl. Phys Letters, Vol 61, No. 10, Sep			
c 	-	cw	Morgan et al., "Hybrid Dielectric/AlGaAs Mirro Emitting Laser", Appl. Phys. Letters, Vol. 66, N	or Spatially Filtered Vertical C No. 10, March 6, 1995, pp. 115	Cavity Top-Surface 57-1159.	
? 		cx	Morgan et al., "Novel Hibrid-DBR Single-Mod Record Low Voltage", 2 pages, dated prior to D		ing VCSEL with	
, 	\int	CY	Morgan et al., "Progress and Properties of High Laser Arrays", SPIE, Vo. 1850, January 1993, p	-Power Coherent Vertical Cav pp. 100-108.	rity Surface Emitting	
 ,		cz	Morgan et al., "Progress in Planarized Vertical SPIE, Vol. 1562, July 1991, pp. 149-159.		Devices and Arrays",	
9		DA	Morgan et al., "Submilliamp, Low-Resistance, Overtical-Cavity Surface Emitting Lasers", Hone			

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BZ	5,818,066	10/06/1998	Duboz		257	21	
CA	5,903,590	05/11/1999	Hadley et al.		372	96	
/ CB	5,940,422	08/17/1999	Johnson		372	45	
/ cc	5,978,401	11/02/1999	Morgan		372	50	
CD	6,055,262	04/25/2000	Cox et al.		372	96	
FOREIGN PATENT DOCUMENTS							
	Document No	Date	Co	ountry	Class	Su Cla	
CE	JP 5-299779	11/12/19	93 Japan				Yes
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
CF Banwell et al., "VCSE Laser Transmitters for Parallel Data Links", IEEE Journal of Quantum Electronics, Vol. 29, No. 2, February 1993, pp. 635-644.							
CG	Catchmark et al., Lasers", CLEO 1	"High Tempera			ical Cavity	Top S	urface-Emitting
CH Chemla et al., "Nonlinear Optical Properties of Semiconductor Quantum Wells", Optical Nonlinearities and Instabilities in Semiconductors, Academic Press, Inc., Copyright 1988, pp. 83- 120.							
CH	Nonlinearities and 120.	d Instabilities ir	1 Semiconducto	ors, Academi		, 1	yright 1988, pp. 63-
CI	Nonlinearities and 120.	ı-Speed Modula	ation of Vertica	ıl-Cavity Sur	face-Emitti	•	sers", IEEE Photonics
	Nonlinearities and 120. Choa et al., "High Technology Lette G. G. Ortiz, et al.,	n-Speed Modular, Vol. 3, No. 8, "Monolithic Interce-Enhance	ation of Vertica , August 1991, ntegration of In d Quantum We	ll-Cavity Sur pp. 697-699 0.2 GA0.8A	face-Emitti	ng Las	sers", <u>IEEE Photonics</u>
CI	Nonlinearities and 120. Choa et al., "High Technology Lette G. G. Ortiz, et al., Lasers with Reson 13, June 20, 1996	n-Speed Modular, Vol. 3, No. 8 , "Monolithic In nance-Enhanced , pp. 1205-120	ation of Vertica August 1991, ntegration of In d Quantum We	al-Cavity Sur pp. 697-699 0.2 GA0.8A Il Photodetec	face-Emitti s Vertical Cetors", Elec	ng Las	sers", <u>IEEE Photonics</u> Surface-Emitting

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FORM PTO-1449	Atty. Docket No.: 1100.1114101 (H16-2654	Serial No.: 09/751,423
OVPLET OF PATENTS AND PUBLICATIONS FOR	Applicant: Robert A. M	organ et al.
OTPLETOF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION SI DISCLOSURE STATEMENT	Filing Date	Group Art:
	December 29, 2000	2872
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Me		DB	Morgan et al., "Transverse Mode Control of Vertical-Cavity Top-Surface Emitting Lasers", <u>IEEE Photonics Technology Letters</u> , Vol. 4, No. 4, April 1993, pp. 374-377.	
C.			рc	Morgan et al., "Vertical Cavity Surface Emitting Laser Arrays: Come of Age,", Invited paper, <u>SPIE</u> , Vol. 2683-04, OE LASE 96; Photonics West: Frabrication, Testing and Reliablity of Semiconductor Lasers, (SPIE< Bellingham, WA, 1996).
<i>O</i> ''			DD ·	Morgan et al., "Vertical-Cavity Surface-Emitting Laser Arrays" SPIE, Vol. 2398, February 1995, pp. 65-93.
·ð			DE	Morgan, "High-Performance, Producible Vertical Cavity Lasers for Optical Interconnects", <u>High Speed Electronics and Systems</u> , Vol. 5, No. 4, December 1994, pp. 65-95.
C.			DF	Morgan, "Transverse Mode Control of Vertical-Cavity Top-Surface Emitting Lasers", <u>IEEE Phot.</u> Tech. Lett., Vol. 4, No. 4., p. 374, April 1993.
î			DG	Nugent et al., "Self-Pulsations in Vertical-Cavity Surface-Emitting Lasers", <u>Electronic Letters</u> , Vol. 31, No. 1, January 5, 1995, pp. 43-44.
0			DH	U.S. Patent Application Serial No. 09/751,422, filed December 29, 2000, entitled "Resonant Reflector for Use with Optoelectronic Devices".

EXAMINER: Vougla Will DATE CONSIDERED: 1 Lec 03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.